

	Hits	Search Text	DBs	Time Stamp
1	697	("257/347-348").CCLS.	USPAT	2001/10/03 21:46
2	1937	((("257/347-348,351,369") or ("438/353,149")).CCLS.	USPAT	2001/10/03 21:46
3	120	(((((eib not protein) not eib-n\$8.in.) not eib.in.) not eib adj et adj al) not nicholas adj4 eib) not (536/23.2 536/23.6 536/24.5 435/419 435/468 435/252.3 800/298 800/286).ccls.) not erasure) not encader.adj.inboundl.not.eib.adj.lan.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/03 12:01
4	198	eib not protein	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/03 11:44
5	251	eib	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/03 11:42
6	107	body adj effect and soi	USPAT	2001/01/31 08:00
7	104	depletion adj region WITH mos	USPAT	2001/01/30 18:10
8	3660	depletion adj region	USPAT	2001/01/30 18:09
9	188	((("257/347-348").CCLS.) and (mos oxide)) and (bias threshold) and charge	USPAT	2001/01/30 17:09
10	379	((("257/347-348").CCLS.) and (mos oxide)) and (bias threshold)	USPAT	2001/01/30 17:08
11	19	"Dynamic threshold voltage mosfet"	USPAT	2001/01/30 15:33
12	362	accumulation adj mode	USPAT	2001/01/30 15:33
13	62	(accumulation adj mode) and mosfet	USPAT	2001/01/30 15:33
14	23	((("257/347-348").CCLS.) and (mos oxide)) and (bias threshold) and standby	USPAT	2001/01/30 09:59
15	1	("5559368").PN.	USPAT	2001/01/30 09:56
16	1	("5616944").PN.	USPAT	2001/01/30 09:49
17	848	nfet	USPAT	2001/01/29 18:04
18	172	hiroo.in. and masuda.in.	JPO	2001/01/29 17:35
19	1	hiroo.in. and masuda.in.	DERWENT	2001/01/29 17:34
20	32	((hiroo).in) and masuda.in.	USPAT	2001/01/29 17:32
21	0	((hiroo).in) and masudo.in.	USPAT	2001/01/29 17:31
22	0	((((hiroo).in) and masuda.in.) and tsunemo.in)	USPAT	2001/01/29 17:31
23	1335	(hiroo).in	USPAT	2001/01/29 17:30
24	0	"variable threshold voltage mosfet"	USPAT	2001/01/29 16:58
25	48	vtnos	USPAT	2001/01/29 16:07
26	11	((("257/347-348").CCLS.) and (mos oxide)) and (dynamic adj threshold)	USPAT	2001/01/29 16:06
27	0	((("257/347-348").CCLS.) and (mos oxide)) and (dynamic adj threshold near mos)	USPAT	2001/01/29 15:36
28	7	((("257/347-348").CCLS.) and (mos oxide)) and (bias threshold) and accumulation adj mode	USPAT	2001/01/29 15:34

	Hits	Search Text	DBs	Time Stamp
29	7	((("257/347-348").CCLS.) and (mos oxide)) and (bias threshold) and "accumulation mode"	USPAT	2001/01/29 15:29
30	1	"5359219".PN.	USPAT	2001/01/29 15:16
31	1	"5641980".PN.	USPAT	2001/01/29 15:15
32	1	"5923067".PN.	USPAT	2001/01/29 15:15
33	1	"5294821".PN.	USPAT	2001/01/29 15:15
34	1	"5923067".PN.	USPAT	2001/01/29 15:13
35	1	"5892256".PN.	USPAT	2001/01/29 14:21
36	1	"5945712".PN.	USPAT	2001/01/29 14:21
37	1	"6072217".PN.	USPAT	2001/01/29 14:21
38	1	"5608252".PN.	USPAT	2001/01/29 14:20
39	654	((("257/347-348").CCLS.) and (mos oxide))	USPAT	2001/01/29 13:58
40	53	accumulation adj mode and 257/3\$2.ccls.	USPAT	2001/01/29 12:18
41	26	dtmos	USPAT	2001/01/29 11:58
42	0	electrically adj induced adj body	USPAT	2001/01/29 09:37
43	48	vtmos	USPAT	2001/01/29 09:36
44	91	eib	USPAT	2001/01/29 09:06
45	0	eib-mos	USPAT	2001/01/29 09:06
46	0	eib and vtmos and 257/\$3.ccls.	USPAT	2001/01/29 09:01
47	0	eib and vtmos	USPAT	2001/01/29 09:01